

cont.
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thus obtained. If the first oxidized sidewalls [3740] 37-40 are formed during the RIE. it is believed that lesser control would result in an alteration of the profile of the first sidewalls 33-36 due to the removal of some of the material in the first FOX insulator layer 22.

In the claims:

Please add the following new claims 32 - 35.

rule 2 >

32. The integrated circuit semiconductor device as claimed in claim 27, wherein said first protective layer is a barrier layer.

33. The integrated circuit semiconductor device as claimed in claim 27, wherein said first protective layer on said sidewalls of said flowable oxide insulator layer has a thickness equal to or less than 20% of a thickness of said flowable oxide insulator layer.

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34. The integrated circuit semiconductor device as claimed in claim 27, wherein said first protective layer on said sidewalls of said flowable oxide insulator is a low-K dielectric.

35. The integrated circuit semiconductor device as claimed in claim 34, wherein said first protective layer on said sidewalls of said flowable oxide insulator layer has a thickness equal to or less than 20% of a thickness of said flowable oxide insulator layer.
